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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Shunpei Yamazaki, et al. Art Unit : 1765
Serial No. : 09/892,225 Examiner : Mathew J. Song
Filed : June 25, 2001
Title : SEMICONDUCTOR DEVICE AND FABRICATION METHOD THEREFOR

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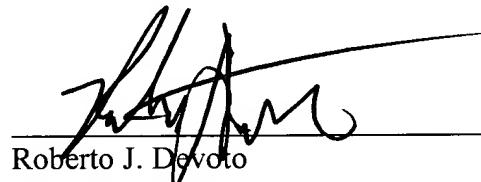
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Supplemental to an Information Disclosure Statement filed on November 22, 2004, Applicants submit a partial translation of Desig. ID "AO". This partial translation was inadvertently omitted from the original filing. A copy of the reference listed on the attached form PTO-1449 is enclosed along with the partial translation.

Please apply any relevant charges or credits to Deposit Account No. 06-1050.

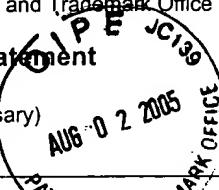
Respectfully submitted,



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Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 07977-279001	Application No. 09/892,225
Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Shunpei Yamazaki, et al.	
		Filing Date June 25, 2001	Group Art Unit 1765



U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						

Foreign Patent Documents or Published Foreign Patent Applications							
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation
							Yes
	AJ	JP 04-168769	06/16/1992	Japan			FULL
	AK						
	AL						
	AM						
	AN						

Other Documents (include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
	AO	Sasaki et al., "A New Low-Temperature Poly-Si TFT Technology Realizing Mobility above 500 cm ² /Vs by Using CW Laser Lateral Crystallization (CLC)", Journal of Institute of Electronics, Information and Communication Engineers, C, Vol. J85-C, No. 8, pp. 601-608, August 2002. [PARTIAL TRANSLATION ENCLOSED].
	AP	
	AQ	

Examiner Signature	Date Considered
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	